

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Cancelled)
2. (Previously Presented) A mask comprising:
a circuit pattern to be transferred to a substrate via an optical system; and
an inspection pattern to be used for a measurement of a line width of a pattern transferred to said substrate,
wherein said inspection pattern includes:
a first measurement pattern;
a second measurement pattern to be superimposed on an image of said first measurement pattern; and
an extraction pattern to be superimposed on an image of said first measurement pattern and an image of said second measurement pattern, and to be used for an extraction of a predetermined image from a superimposed image of said first measurement pattern and said second measurement pattern.
3. (Original) A mask according to claim 2, wherein each of said first measurement pattern and said second measurement pattern comprises a plurality of linear patterns which are parallel to each other, and said extraction pattern has a shape which can extract at least one approximate rhombic shape image from an image to be formed by superimposing said first measurement pattern and said second measurement pattern intersecting at a predetermined angle.
4. (Previously Presented) A mask according to claim 2, wherein said inspection pattern is formed in a separate area to a circuit pattern area in which said circuit pattern is formed.

5. (Previously Presented) A mask according to claim 2, wherein said inspection pattern is a part of said circuit pattern.

6. (Previously Presented) A mask according to claim 2, wherein a line width of said inspection pattern corresponds to a line width of said circuit pattern.

7. - 10. (Cancelled)

11. (Previously Presented) A mask comprising:
a base member;
a first line-and-space pattern formed on said base member with a predetermined line width; and

a second line-and-space pattern which is to be superimposed on an image of said first line-and-space pattern and which is formed at a predetermined angle with respect to said first line-and-space pattern with a line width different from said predetermined line width.

12. (Previously Presented) A mask according to claim 11, wherein a circuit pattern is formed in an area different from an area in which said first line-and-space pattern and said second line-and-space pattern are formed.

13. - 14. (Cancelled)

15. (Previously Presented) A mask according to claim 2, wherein said inspection pattern is an isolated pattern.

16. (Previously Presented) A mask according to claim 2, wherein said inspection pattern is a line-and-space pattern.

17. (Previously Presented) A mask comprising:
a base member;
a first measurement pattern formed on said base member;
a second measurement pattern formed on said base member and to be superimposed on an image of said first measurement pattern; and

an extraction pattern formed on said base member and to be superimposed on an image of said first measurement pattern and an image of said second measurement pattern, and to be used for extraction of a predetermined image from a superimposed image of said first measurement pattern and said second measurement pattern.

18. (Previously Presented) A mask according to claim 17, wherein a line width of said first measurement pattern and said second measurement pattern corresponds to a line width of a circuit pattern.

19. (Previously Presented) A mask according to claim 17, wherein said first measurement pattern and said second measurement pattern are isolated patterns.

20. (Previously Presented) A mask according to claim 17, wherein said first measurement pattern and said second measurement pattern each is a line-and-space pattern.

21. (Previously Presented) A mask according to claim 17, wherein a line width of said first measurement pattern is different from a line width of said second measurement pattern.

22. (Cancelled)

23. (Previously Presented) A mask according to claim 11, further comprising an extraction pattern to be used for an extraction of a plurality of diamond-shaped images from a superimposed image of said first line-and-space pattern and said second line-and-space pattern.

24. (Previously Presented) A mask according to claim 17, wherein said extraction pattern is used to extract a diamond-shaped image from a superimposed image of said first measurement pattern and said second measurement pattern.